

ABSTRACT OF THE INVENTION

A capacitor is configured by a bottom electrode BE, an inter-electrode dielectric D, and a top electrode TE. Directly under the bottom electrode BE, for example, silicon oxide (SiO_2) is disposed, and directly above the top electrode TE as well, for example, silicon oxide (SiO_2) is disposed. The capacitor is covered with an insulating layer Low-k having a low dielectric constant. The insulating layer Low-k is formed from a material having as low of a dielectric constant as possible in order to reduce the parasitic capacitance between wirings. High-dielectrics High-k for suppressing the swelling of electric lines of force are disposed on side walls of an inter-electrode dielectric D. A dielectric constant of the High-dielectric High-k is at least higher than a dielectric constant of the insulating layer Low-k.